## NSN 5961-00-378-0474

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-378-0474 **Inclosure Material:** Metal **Overall Length:** 1.050 inches Overall Diameter: 2.200 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Gate **Mounting Method:** Press fit **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1300.0 nonrepetitive peak reverse voltage, peak total value and 1200.0 repetitive peak reverse voltage, peak total value and 1.85 forward voltage, peak and 5.0 peak negative gate voltage and 3.5 gate trigger voltage, dc **Current Rating Per Characteristic:** 5000.00 amperes forward current, average preset and 250.00 milliamperes forward current, total rms preset and 500.00 milliamperes forward current, total rms peak and 350.00 amperes forward current, total rms megahertz **Power Rating Per Characteristic:** 16.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Gate wire leads to betwisted and 30.000 in. Lg; junction pattern arrangement: pnpn **Terminal Type And Quantity:** 2 ferrule and 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: